Complementary Silicon Power Transistors

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- . . . designed for general-purpose switching and amplifier applications.
- DC Current Gain hFE = 20-70 @ IC = 4 Adc
- Collector-Emitter Saturation Voltage -WWW.DZSC.COM VCE(sat) = 1.1 Vdc (Max) @ IC = 4 Adc
- Excellent Safe Operating Area

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	VCEO	60	Vdc
Collector–Emitter Voltage	VCER	70	Vdc
Collector–Base Voltage	V _{CB}	100	Vdc
Emitter-Base Voltage	V _{EB}	7	Vdc
Collector Current — Continuous	lC	15	Adc
Base Current D1	ΙΒ	7	Adc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	PD	115 0.657	Watts W/°C
Operating and Storage Junction Temperature Range	TJ, T _{stg}	-65 to +200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	R ₀ JC	1.52	°C/W

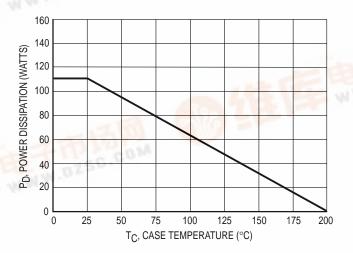


Figure 1. Power Derating

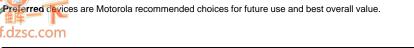
NPN 2N3055* **MJ2955**

*Motorola Preferred Device

15 AMPERE **POWER TRANSISTORS COMPLEMENTARY SILICON 60 VOLTS 115 WATTS**



CASE 1-07 TO-204AA (TO-3)



2N3055 MJ2955

ELECTRICAL CHARACTERISTICS ($T_C = 25$ °C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
*OFF CHARACTERISTICS				
Collector–Emitter Sustaining Voltage (1) (I _C = 200 mAdc, I _B = 0)	VCEO(sus)	60	_	Vdc
Collector–Emitter Sustaining Voltage (1) (IC = 200 mAdc, R _{BE} = 100 Ohms)	VCER(sus)	70	_	Vdc
Collector Cutoff Current (V _{CE} = 30 Vdc, I _B = 0)	ICEO	_	0.7	mAdc
Collector Cutoff Current (V _{CE} = 100 Vdc, V _{BE(off)} = 1.5 Vdc) (V _{CE} = 100 Vdc, V _{BE(off)} = 1.5 Vdc, T _C = 150°C)	ICEX		1.0 5.0	mAdc
Emitter Cutoff Current $(V_{BE} = 7.0 \text{ Vdc}, I_{C} = 0)$	IEBO	_	5.0	mAdc
*ON CHARACTERISTICS (1)	•			
DC Current Gain (I _C = 4.0 Adc, V _{CE} = 4.0 Vdc) (I _C = 10 Adc, V _{CE} = 4.0 Vdc)	hFE	20 5.0	70 —	_
Collector–Emitter Saturation Voltage (I _C = 4.0 Adc, I _B = 400 mAdc) (I _C = 10 Adc, I _B = 3.3 Adc)	VCE(sat)	_	1.1 3.0	Vdc
Base–Emitter On Voltage (I _C = 4.0 Adc, V _{CE} = 4.0 Vdc)	VBE(on)	_	1.5	Vdc
SECOND BREAKDOWN				
Second Breakdown Collector Current with Base Forward Biased (V _{CE} = 40 Vdc, t = 1.0 s, Nonrepetitive)	I _{S/b}	2.87	_	Adc
DYNAMIC CHARACTERISTICS				
Current Gain — Bandwidth Product (IC = 0.5 Adc, V _{CE} = 10 Vdc, f = 1.0 MHz)	fΤ	2.5	_	MHz
*Small–Signal Current Gain (IC = 1.0 Adc, V _{CE} = 4.0 Vdc, f = 1.0 kHz)	h _{fe}	15	120	
*Small–Signal Current Gain Cutoff Frequency (V _{CE} = 4.0 Vdc, I _C = 1.0 Adc, f = 1.0 kHz)	f _{hfe}	10	_	kHz

^{*} Indicates Within JEDEC Registration. (2N3055)

⁽¹⁾ Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

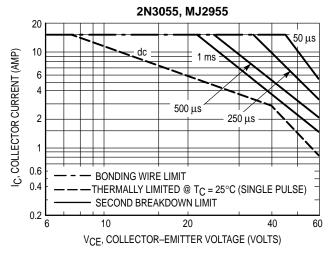


Figure 2. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_{\text{C}} - V_{\text{CE}}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 2 is based on $T_C=25^{\circ}C$; $T_{J(pk)}$ is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10% but must be derated for temperature according to Figure 1.

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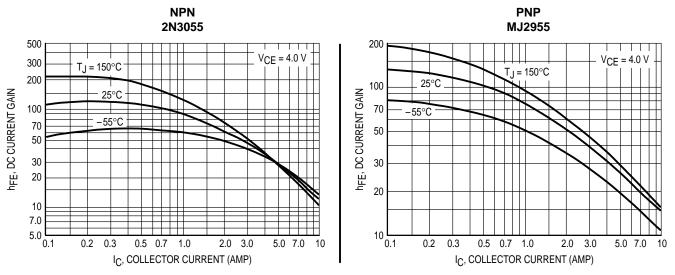


Figure 3. DC Current Gain

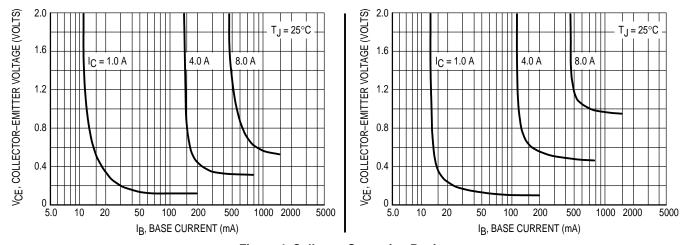


Figure 4. Collector Saturation Region

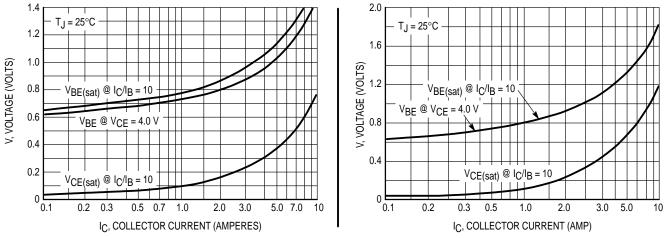
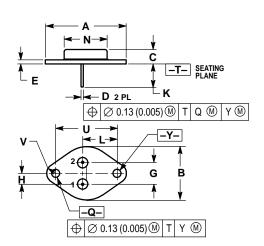


Figure 5. "On" Voltages

PACKAGE DIMENSIONS



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
 Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.
- ALL RULES AND NOTES ASSOCIATED WITH
 REFERENCED TO-204AA OUTLINE SHALL APPLY.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	1.550 REF		39.37 REF	
В		1.050		26.67
С	0.250	0.335	6.35	8.51
D	0.038	0.043	0.97	1.09
E	0.055	0.070	1.40	1.77
G	0.430	BSC	10.92 BSC	
Н	0.215 BSC		5.46 BSC	
K	0.440	0.480	11.18	12.19
L	0.665 BSC		16.89 BSC	
N		0.830		21.08
Q	0.151	0.165	3.84	4.19
U	1.187	BSC	30.15 BSC	
٧	0.131	0.188	3.33	4.77

STYLE 1:
PIN 1. BASE
2. EMITTER
CASE: COLLECTOR

CASE 1-07 TO-204AA (TO-3) ISSUE Z

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